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应用于激光微显示中高速扫描的压电 MEMS 微镜

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摘要:设计并制作了一款直径为 1.1 mm、频率为 31.11 kHz 的 MEMS 压电微镜, 用于需要高速扫描且小尺寸的应用场景。该器件所需模态为扭转模态, 与其他模态分离情况好, 不会出现耦合。实验结果显示, 电压为 32 V 时光学扫描角 40.66°, 品质因子 1 155。改变 PZT 极性, 实验得到了薄膜材料的铁电性质影响。另外, 完成了 MEMS 微镜在 0 °C~100 °C 不同温度下角度的变化实验, 偏离不超过 ±1°。仿真模拟、实验结果和理论计算结果三者拟合情况好, 表明该设计的微镜具有较高的可控性和稳定性, 为实现高精度扫描提供了有力支持。该 MEMS 压电微镜在 AR/VR 等领域中具有潜在的应用前景。

关键词:压电微镜; 压电陶瓷; 微机电系统; 激光光束扫描; AR/VR

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0 引言

近年来, 随着元宇宙的概念得到了极大的关注, 在增强现实(Augmented Reality, AR)、虚拟现实(Virtual Reality, VR)和混合现实(Mixed Reality, MR)技术发展的推动下, 包含微机电系统(Micro-Electro-Mechanical System, MEMS)微镜的激光束扫描(Laser Beam Scanning, LBS)已经广泛应用于微型显示领域^[1]。例如, 微软的 Hololens 2 AR 头盔。LBS 技术是一种全反射技术, 通过一个微小的镜面进行投影, 不需要复杂的光学系统。相比于其他微显示技术, LBS 具有更好的颜色鲜艳度、更高的亮度以及更高的对比度。LBS 能够实现高分辨率、高亮度的微型显示。

MEMS 微镜是 LBS 中重要的光学器件^[2], 在所有可用于微镜驱动的方法中, 静电、电磁、电热、压电驱动是最常用的四种^[3]。静电驱动需要高电压, 以产生足够的力来驱动微镜, 这给实际 VR 应用带来一些挑战^[4]。电磁驱动可以产生足够的力来驱动微镜, 但需要大量的电流来激励, 这会导致一些不可避免的热量和功耗问题, 且封装体积较大^[5]。电热驱动响应速度相对较慢, 因此不适合用于需要快速响应的 AR/VR^[6]。而压电材料具有高的驱动效率和响应速度, 可以在微秒级别内完成驱动。同时, 压电材料具有可逆性, 因此可以在不需要太多能量的情况下进行反复驱动。另外压电驱动不同于电磁驱动无需外界材料帮助提供驱动力, 只依靠本身的压电特性对 MEMS 微镜进行驱动, 因而能够实现小尺寸, 使压电材料适合于微型设备。

常用在 MEMS 微镜的压电薄膜材料^[7]有 AlN、AlScN 和压电陶瓷(Piezoelectric Ceramic, PZT)三种。在压电微镜制造方面, AlN, AlScN 具有与半导体工艺兼容、线性度较好、高稳定性和低热漂移等优点。但是, AlN^[8]和 AlScN^[9]的压电系数较低, 驱动力较弱, 所需驱动电压高, 不适合大转角微镜。PZT 是一种常用的压电材料, 虽然与半导体工艺的兼容性相对较差, 但是具有高压电响应、较高的压电系数和较高的稳定性等优

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点,适用于制造微显示压电微镜。

本文设计了一款直径为 1.1 mm、频率为 31 kHz 的微镜。测试结果显示在 32 V 可以稳定达到 40.66°, 品质因子(Quality factor, Q)为 1 155。在改变 PZT 极性的情况下,可以观察到薄膜材料的铁电性质对微镜的影响,在 0 °C~100 °C 温度下,角度的偏离不超过 ±1°。

1 设计与仿真

1.1 驱动原理

压电驱动的原理是施加外部电场引发压电材料的形变,并导致部分结构发生位移。本文中的驱动结构由厚度为 40 μm 的硅上绝缘体(Silicon-On-Insulator, SOI)器件层、两侧电极和 PZT 薄膜构成,其驱动原理如图 1 所示。驱动器的底部和顶部涂覆有氧化铱(IrO)和金(Au)导电薄膜。在未施加电压时,驱动器、扭转梁和镜面与 X 轴保持水平,如图 1(a)所示。利用 PZT 的逆压电效应,在电极之间施加电压(左、右两侧的驱动电压反相),左侧的 PZT 薄膜会收缩,从而在 Si 梁的上表面产生纵向拉应力;而右侧的 PZT 薄膜会伸长,导致梁的上表面产生压应力。因此,微驱动的尖端沿 Z 方向发生位移,使得梁呈 S 形弯曲,如图 1(b)所示。这种扭转运动传递到微镜,用于触发机械共振以进行快速扫描。

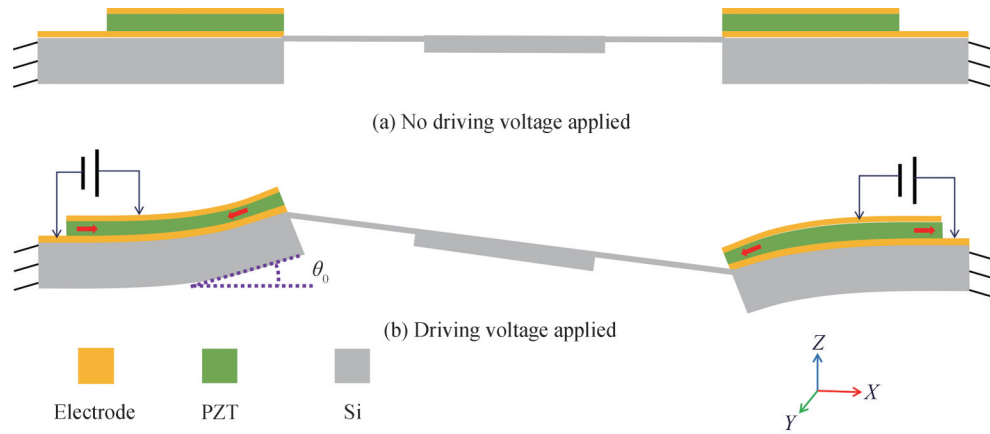


图 1 压电微镜驱动的原理

Fig. 1 The principle of piezoelectric micro mirror driving

对于复合多层压电悬臂梁,要计算尖端位移,首先找到梁的受力中性轴^[10]

$$\bar{Z} = - \frac{\sum_{i=1}^N E_i t_i^2 - 2 \sum_{i=1}^N E_i t_i \sum_{j=1}^i t_j}{2 \sum_{i=1}^N E_i t_i} \quad (1)$$

式中, \bar{Z} 是距离 Si 底面的 Z 轴垂直距离; t_i 是 i 层的厚度; E_i 是第 i 层的杨氏模量; $i=1, 2, \dots, 6$ 分别是 Si/SiO₂/IrO/PZT/Au/SiO₂ 层。表 1 是各层的物理参数。

表 1 多层复合梁的物理参数

Table 1 Physical parameters of multi-layer composite beams

Material	Si	SiO ₂	IrO	PZT	Au	SiO ₂
Young's modulus/GPa	170	70	168	60.61	70	70
Thickness/μm	40	0.2	0.17	2	0.2	2

在多层驱动梁中产生的力矩可以通过第 4 层 PZT 薄膜产生的力矩 M_{PZT} 来计算,作为逆压电效应的结果有

$$M_{PZT} = \frac{1}{2} \omega E_4 d_{31} V \left(2\bar{Z} - 2 \sum_{i=1}^4 t_i + t_4 \right) \quad (2)$$

式中, ω 是驱动部分的宽度,在本文的设计中,近似估计为梯形的中线位置, d_{31} 是压电系数, V 是所施加的电压幅值。6 层复合梁结构的总抗弯刚度 C 表示为^[10]

$$C = \frac{1}{3} \sum_{i=1}^N E_i w \left[3t_i \left(\bar{Z} - \sum_{j=1}^i t_j \right) \left(\bar{Z} - \sum_{j=1}^{i-1} t_j \right) + t_i^3 \right] \quad (3)$$

将驱动模型视为附接到基底,而没有在连接梁的另一端设置边界条件。长为 l 的驱动器尖端处的静态角度 θ_0 近似为

$$\theta_0 = \frac{M_{\text{PZT}} l}{C} \quad (4)$$

对于谐振状态的微镜,用质量-阻尼-弹簧的二阶振动系统来表达,方程为

$$M_{\text{PZT}} = I \frac{d^2 \theta}{dt^2} + c \frac{d\theta}{dt} + K\theta \quad (5)$$

式中, I 为振镜的转动惯量, c 为阻尼系数, K 为扭转轴的弹性常量。当微镜的驱动信号频率与共振频率相等时,谐振状态的 θ_{res} 转动角度为

$$\theta_{\text{res}} = \theta_0 \frac{\sqrt{IK}}{c} \quad (6)$$

1.2 结构设计

图2是所设计的压电微镜结构。在芯片的中心位置,有一个直径为1.1 mm的反射镜。该反射镜由一对长1.1 mm、宽200 μm 、厚40 μm 的扭转梁支撑。示意图中的浅绿色区域表示压电驱动部分,这个梯形驱动器由两个电极和它们之间的PZT压电层组成。内侧(黄色)和外侧(紫色)的布线表示驱动器顶部电极和底部电极的导线,而8个镀金的PAD用于与PCB板进行电连接,中间的4个PAD用于后续压阻反馈。4个压电驱动器固定在基板的一端,通过连接梁与扭转梁接触,以激励微镜围绕扭杆的旋转轴线进行谐振。为了增强镜板的刚度并抑制镜板的动态变形,SOI硅衬底的一部分被保留作为肋结构。

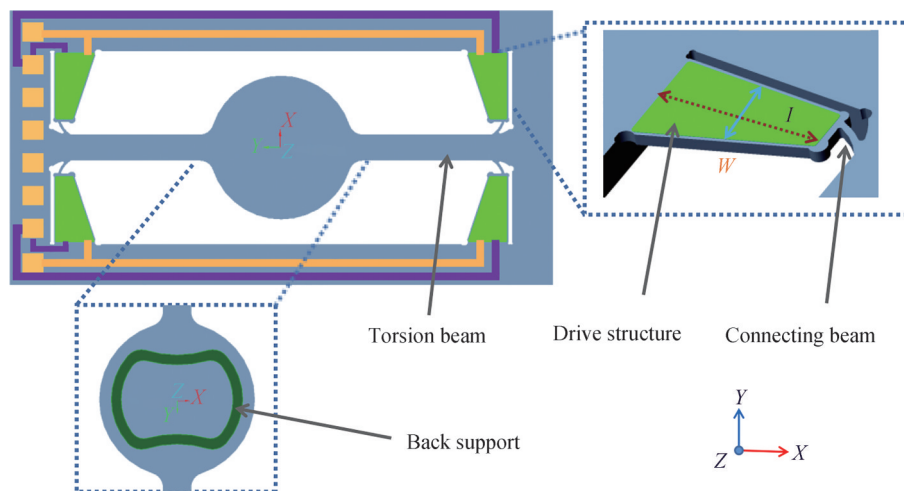


图2 压电微镜结构设计

Fig. 2 Design of piezoelectric micro mirror structure

通过有限元仿真方法(Finite Element Analysis, FEA),可以预测微镜的模式。图3是设计的谐振频率和相应谐振模式的仿真结果。仿真过程中采用了固定约束边界条件,并进行本征频率分析。表2是仿真中使用的重要材料参数。

根据仿真结果,设计的第二模式是扭转模式,也称为光学扫描模式,其频率为31.08 kHz。这个频率能够满足光学扫描的要求。与第一和第三模式(频率分别为17 kHz和60 kHz)相比,频率差异大,模式之间的分离较好,不会发生耦合。该器件的设计目标是在期望的频率下实现40°的光学扫描角度。根据图4显示,在接近31.08 kHz的谐振频率下,最大应力为1 GPa。这个应力低于硅的应力极限,证明此设计的可靠性。

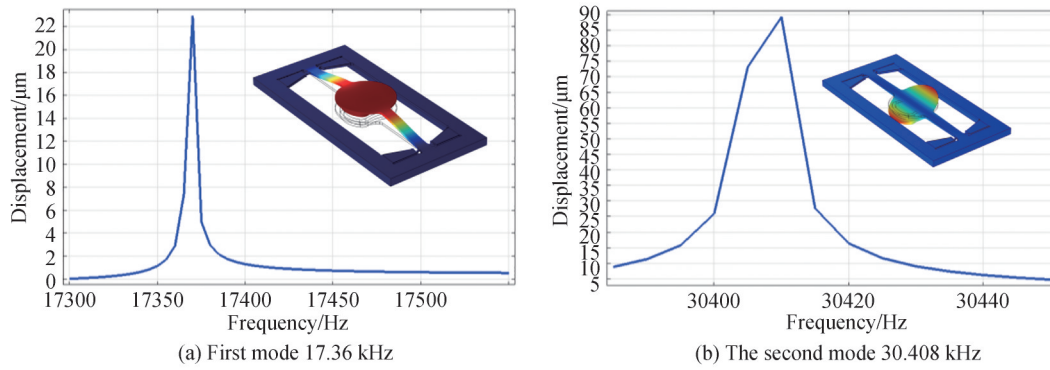


图3 FEM模态分析计算
Fig. 3 FEM analytical modeling

表2 仿真所需物理参数

Table 2 Physical parameters required for simulation

Parameters	Layer thickness/ μm	Young's modulus/GPa	Poisson ratio	Density/ $(\text{kg}\cdot\text{m}^{-3})$	$d_{31}/(\text{pm}\cdot\text{V}^{-1})$
Silicon	40	170	0.3	2 329	N/A
PZT	2	60.61	0.28	7 500	-110

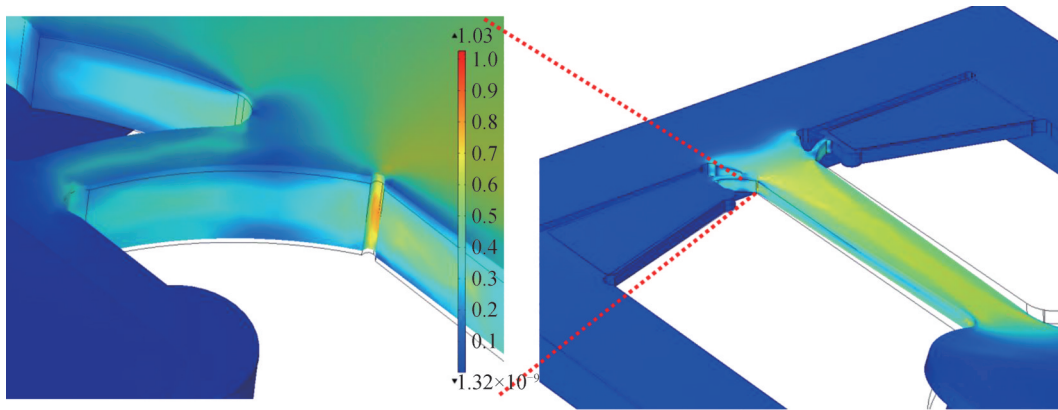


图4 FEM最大应力
Fig. 4 FEM maximum stress

2 制备工艺

在充分设计和仿真准备后,对器件进行加工。图5详细展示了压电MEMS扫描镜的制造流程。首先,在SOI的器件层上沉积了厚度为170 nm的IrO底电极层和厚度为2 μm 的PZT压电薄膜,如图5(a)。接下来,采用电感耦合等离子体(Inductively Coupled Plasma, ICP)技术对PZT层进行刻蚀,并通过离子束刻蚀(Ion Beam Etching, IBE)对底电极进行刻蚀,如图5(b)。随后,使用Lift-Off工艺制备出厚度为200 nm的Au顶电极,并对PZT的电容进行测试,结果显示电容为2.06 nF,如图5(c)。为了防止PZT薄膜中的铅挥发并为顶电极导线留出通孔,采用等离子体增强化学气相沉积(Plasma Enhanced Chemical Vapor Deposition, PECVD)方法沉积了厚度为2 μm 的氧化硅薄膜,如图5(d)。随后,在顶电极导线上进行电镀处理,如图5(e)。接下来,通过深反应离子刻蚀(Deep Reactive Ion Etching, DRIE)技术对器件层进行刻蚀,直到达到埋氧层,形成微镜的镜面、扭转梁、连接梁和驱动结构,如图5(f)。为了支撑镜板下方的结构,采用DRIE技术对背面进行刻蚀,并通过反应离子刻蚀释放整个结构,如图5(g)。通过以上步骤,成功制造了压电MEMS扫描镜。

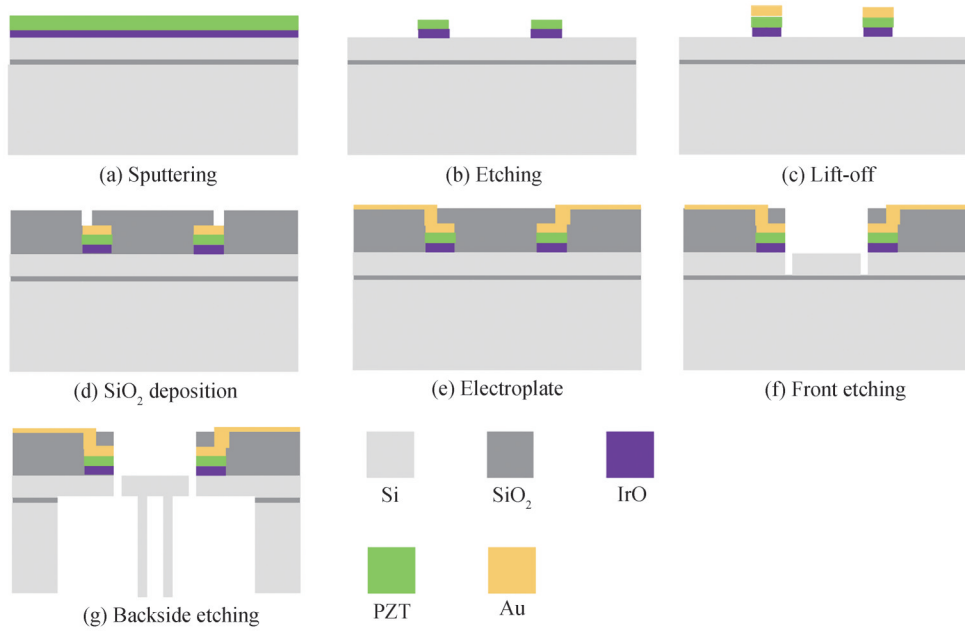


图5 压电微镜的工艺流程
Fig. 5 Process flow of piezoelectric micro mirrors

3 实验测试

3.1 压电性能

铁电反转功能模块在 AFM 测试中用于研究铁电薄膜的单点压电性能,并反映样品的压电性^[12]。该模块施加 10 V 的驱动交流电压,得到 PZT 铁电薄膜的单点压电响应曲线如图 6,该曲线呈现出 180°电畴切换的矩形环和明显的蝴蝶曲线。矩形相位环相对于 $V=0$ 不严格对称,是由于存在干扰电场所致。

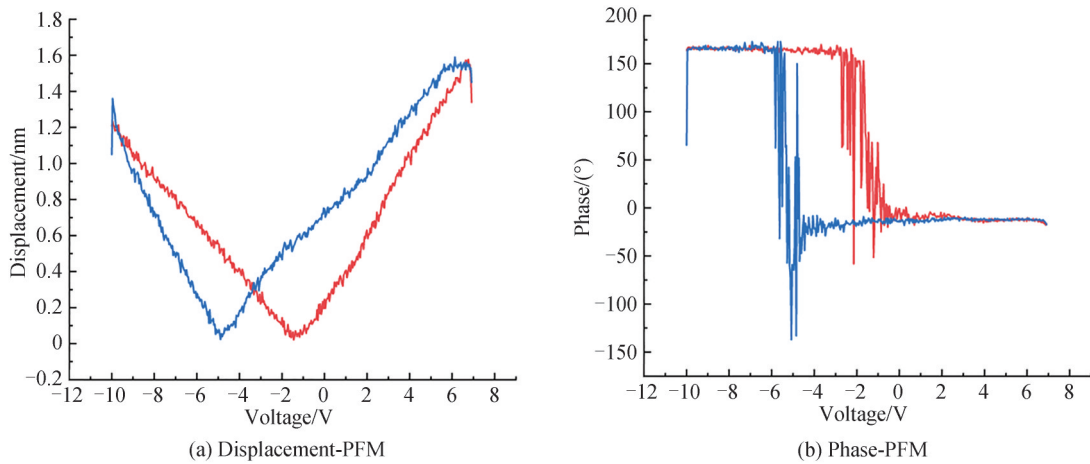


图6 PFM 压电测试结果
Fig. 6 PFM piezoelectric test results

在微观层面下测试结果显示,该薄膜的压电系数为 $d_{33\text{test}}=155 \text{ pm/V}$ 。根据文献[13]考虑了位移和压电效应的连续性条件,在仿真中,压电常数设置为 $d_{33\text{theory}}=600 \text{ pm/V}$,最大位移为 4.82 nm , $d_{33\text{simulation}}=482 \text{ pm/V}$,根据公式

$$d_{33} = d_{33\text{test}} \frac{d_{33\text{theory}}}{d_{33\text{simulation}}} \quad (7)$$

可得 $d_{33}=192.2 \text{ pm/V}$,这是 PZT 的本征压电常数,可以用于模拟仿真计算。

3.2 微镜的转角测试

实验中使用的角度测量装置如图7所示。由下方激光器发射的入射光被微镜反射,反射光聚焦呈现在屏幕中。在此示意图中当镜子最初未被偏置时,屏幕垂直于反射光放置和固定。测量采用的输出信号为直流偏置的方波信号,其中,相位差为 π 的两个信号分别施加到放置在外部框架上的两组驱动器上,如图1(b)所示。微镜产生的反射光将偏离原始光路,屏幕上的光点将发生偏移,偏移距离记为 L 。测量 L 和已知的屏幕到反射镜的距离 H ,可以推导出光学角度 θ_{opt} ,其定义为偏置状态的光路之间形成的角度。

$$\theta_{opt} = 2\arctan(L/2H) \quad (8)$$

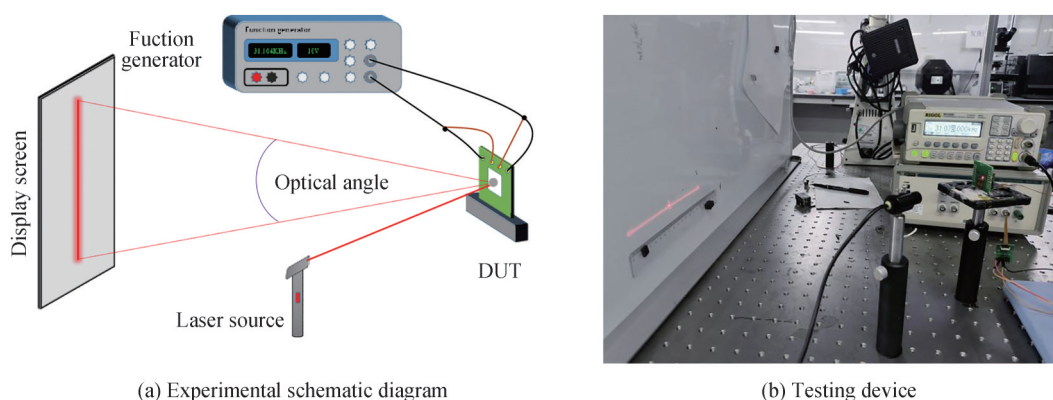


图7 光学测试实验装置

Fig. 7 Optical testing experimental device

3.2.1 频响曲线以及电压位移曲线

在室温下、标准的1个大气压下,对扫描仪的压电驱动性能进行测试。图8展示了反射镜在31.11 kHz基本谐振下通过施加到两组驱动器的激励所产生的光学角度曲线。测量在不同电压下的角度,发现电压为32 V的激励下,当光线垂直入射时,光学扫描角度可达40.66°。随着电压的增大,角度呈近似线性增加,但在电压较大的位置,角度的变化量逐渐变小。这是因为PZT薄膜的非线性特性以及较大阻尼影响。需要注意的是,理论计算结果相对偏大,这是因为在计算中忽略了连接梁的刚性和加强肋结构的弹性常量。

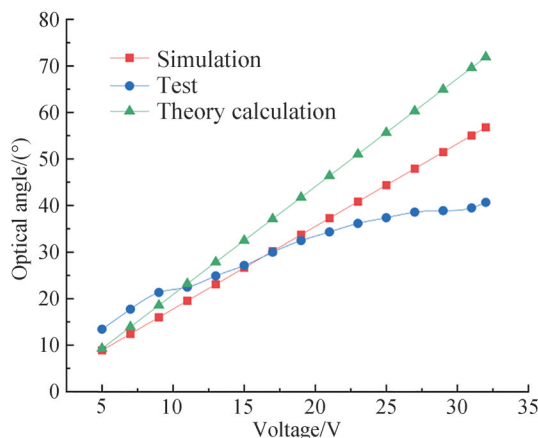


图8 电压角度曲线(测试、仿真、理论计算)

Fig. 8 Voltage angle curve (testing, simulation, theoretical calculation)

对比已有微镜的文献结果(如表3),发现所设计的压电微镜的性能相对较好。不同电压下的频率响应曲线如图9(a)所示,观察到谐振频率与设计仿真结果接近。随着电压的增加,谐振频率也略微增大。这种谐振频率的漂移主要是由于MEMS机械部件的非线性特性引起的^[19]。在图9(b)中,品质因子由频率响应曲线计算得出。可以观察到,随着角度的增大,品质因子逐渐减小。在40.66°的扫描角度下,品质因子仅为1155。

表 3 不同驱动之间的性能对比
Table 3 Performance comparison between different drives

	Driving method	Mirror diameter	Resonant frequency	Resonance angle
ROBERT A ^[14]	ES	$D=0.55$ mm	34 kHz	25°
CHEN M ^[15]	EM	$D=1$ mm	0.56 kHz	28°
TANGUY Q ^[16]	ET	$D=1$ mm	1.19 kHz	16°
GU-STOPPEL S ^[17]	PE	1.1×1.1 mm ²	0.58 kHz	5°
ZHU Y ^[18]	PE	$D=1$ mm	23.9 kHz	21°
Proposed method	PE	$D=1.1$ mm	31 kHz	40.66°

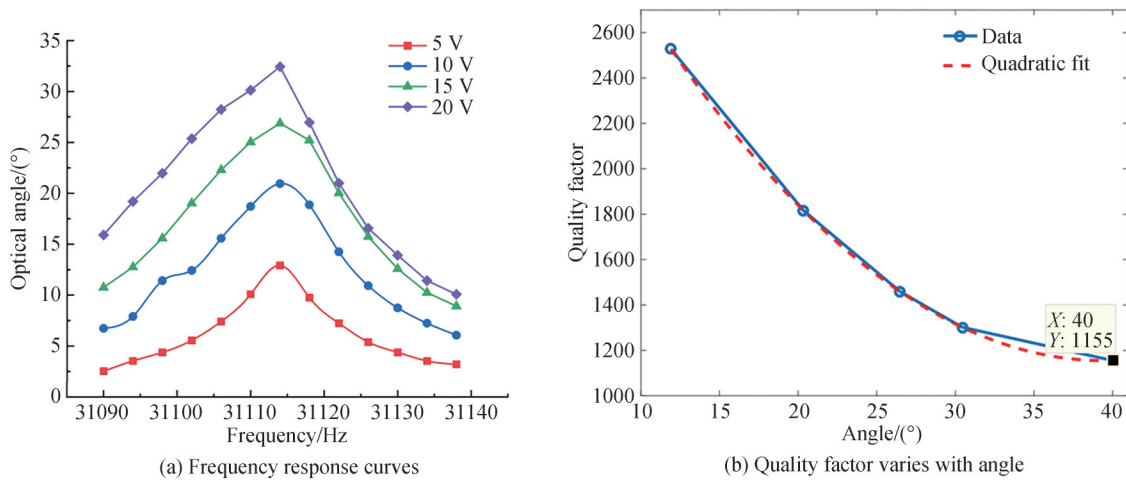


图 9 不同电压下,频响曲线以及品质因子和角度的变化关系

Fig. 9 Frequency response curve under different voltages and relationship between quality factor and angle

3.2.2 极化曲线

在 PZT 上施加不同的电场观察 PZT 材料的极化现象对角度的影响。图 10 是正负电场往复作用下, PZT 材料的角度变化过程。由于 PZT 材料的特性,对称轴并不恰好位于 $V=0$ 的位置,这是由于铁电性质导致的^[20],在未来的工作中应始终保持电压方向的一致性,以避免极化反转导致角度减小。

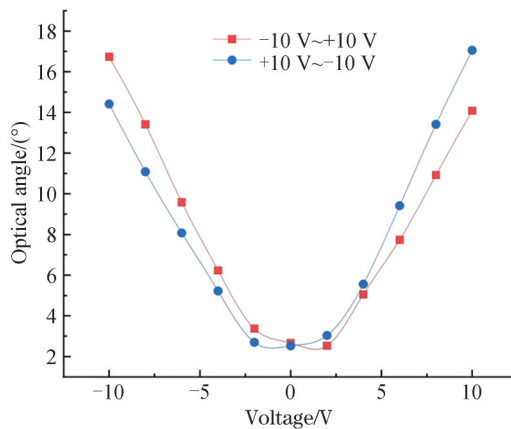


图 10 不同极性下的角度测试
Fig. 10 Angle test at different polarities

3.2.3 温度曲线

为了研究温度对 MEMS 显微镜性能的影响,进行了不同温度下的角度曲线测定,结果如图 11 所示。实验过程中,显微镜首先放置在控制温度的环境中,并逐步升高温度。在每个温度点上,调节信号发生器的输出频

率,找到不同温度对应的谐振频率。观察微镜在谐振频率下的光学角度变化,可以确定不同温度下的角度曲线。从图11可以观察到随着温度的升高,谐振频率逐渐下降。在0~100 °C的温度范围内,谐振频率的漂移达到了30 Hz^[21]。这种漂移可能是由于材料热膨胀、温度相关的阻尼变化或其他热效应导致的。然而,值得注意的是,在这个温度范围内,微镜的角度变化量仅在±1°的范围内,表明在这个工作温度范围内微镜的稳定性。

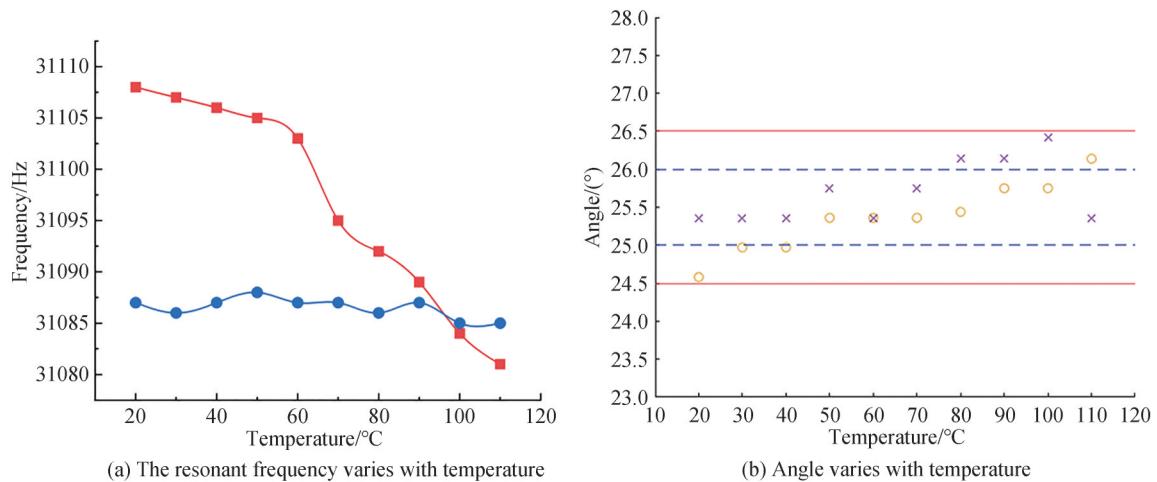


图11 不同温度下的角度、谐振频率测试

Fig.11 Angle and resonant frequency test at different temperatures

在光学扫描角度为40°的条件下,本文所实现的压电微镜在AR领域的应用中,与OQMENTED公司的产品相比,展现了更高的扫描频率,并能在激光显示应用中提供更高的分辨率。与HAMAMATSU公司的电磁驱动产品(S13989-01H)相比,本文所采用的压电驱动方式在频率和角度相近的情况下,能够实现更小的封装体积。

4 结论

本文针对激光微显示应用领域的需求,设计了一种小尺寸、高速大转角的压电MEMS微镜,并进行了验证。仿真结果表明,在目标转角为40°、频率为31.08 kHz时,微镜的最大冯米塞斯应力未超过硅的断裂极限,证明了设计的可靠性。实验中测试了PZT薄膜材料的电学性质,结果显示其本征压电系数 d_{33} 为192.2 pm/V,满足大转角驱动力的需求。测试电压-角度曲线,发现在32 V、31.11 kHz的激励下,微镜能够达到40.66°的转角,且薄膜未发生击穿,结构无损伤,品质因子为1 155。此外,在不同极性下施加电压,验证了PZT薄膜铁电性对器件性能的影响,并指出在未来的工作中应始终保持电压方向的一致性(例如采用加偏值的方波信号),避免极化反转导致角度减小。同时,在0~100 °C的工作范围内,角度变化不超过1°。本文研究可为微显示技术的发展提供有益的参考。

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High Speed Scanning Piezoelectric MEMS Micro Mirrors for Laser Micro Displays

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Abstract: In recent years, with the concept of Metaverse getting great attention, under the promotion of the development of Augmented Reality (AR), Virtual Reality (VR) and Mixed Reality (MR) technologies, the Laser Beam Scanning (LBS) including micro-mirrors of MEMS has been widely used in the field of micro-displays. The LBS technology enables high-resolution, high-brightness micro-displays. MEMS mirrors are important optical devices in LBS due to their compact structure, small size, and fast response speed. Of all the methods available for driving mirrors, piezoelectric driving has a high driving efficiency and response speed, and can be driven in microseconds. At the same time, piezoelectric materials are invertible, so they can be driven repeatedly without too much energy. These properties make piezoelectric materials suitable for fabrication of miniaturized display piezoelectric mirrors. Common piezoelectric thin film materials used in MEMS mirrors include AlN, AlScN, and piezoelectric ceramics

(PZT). In the fabrication of piezoelectric mirrors, AlN and AlScN are compatible with semiconductor processes with fine linearity, high stability and low thermal drift. However, AlN and AlScN have lower piezoelectric coefficient, smaller driving forces, and require higher voltages, which are not suitable for large angle mirrors. PZT is a commonly used piezoelectric material. Although not compatible with semiconductor processes, its high electrical response, high piezoelectric coefficient, and high stability make it suitable for fabrication of miniaturized display piezoelectric mirrors.

To meet the requirements of laser micro display applications, a MEMS piezoelectric mirror with diameter of 1.1 mm, optical angle of 40° and frequency of 31.11 kHz is designed and fabricated, which is suitable for high-speed scanning and small size application scenarios. The large angle piezoelectric MEMS mirror is designed, in which the torsion beam thickness is $40\ \mu\text{m}$, the length is 1.1 mm, the width is $200\ \mu\text{m}$. The results are validated by theoretical calculations and simulation analyses. By using inverse piezoelectric effect, the static angle of PZT multi-layer composite beam with one end fixed and one end free boundary condition under applied voltage is calculated. At the same time, the angle of resonance is calculated by solving the second-order equation of the mass-damped spring. After the calculation, the result is essentially as required. The simulation results show that the required mode of the device is torsion mode, which is well separated from other modes and does not have coupling, and when the target angle is 40° and the frequency is 31.08 kHz, the maximum von Mises stress of the mirror does not exceed the fracture limit of silicon, thus proving the reliability of the design.

In the experiment, the electrical properties of $2\ \mu\text{m}$ PZT thin film material were first tested. It was found to have an intrinsic piezoelectric coefficient d_{33} of 192.2 pm/V and a capacitance of 2.06 nF, meeting the requirements of large-angle driving forces. The complete device was successfully fabricated by multi-step lithography. The test voltage-angle curve shows that under the excitation of 32 V and 31.11 kHz, the mirror can reach an angle of 40.66° , and the thin film does not break down and the structure is not damaged. Tests on the frequency response curves show a quality factor of 1 155. At the same time, resonant frequency drifts are observed at different voltages due to the nonlinearity of the MEMS mechanics. In addition to these tests on device performance under different conditions such as voltage polarity and temperature changes, this study also tested voltage curves applied under different polarities to verify the impact of PZT thin film ferroelectricity on device performance and reminded that in future work, voltage direction should always be consistent (such as using a biased square wave signal) to avoid polarization reversal caused by changes in voltage direction leading to a decrease in angle. Also, we take the curve of device performance as a function of temperature. Within the working range of $0\ ^\circ\text{C}\sim 100\ ^\circ\text{C}$, the angle change does not exceed 1° . In the simulation experiment of the designed micro-mirror, the experimental results are compared with the theoretical calculation results, and it is found that the three fit well, indicating that the designed micro-mirror has a high controllability and stability, and provides strong support for the realization of high-precision scanning.

In further research, the present study plans to introduce piezoresistive or piezoelectric angular feedback modules and implement closed-loop control to improve the performance of such devices. This will provide higher accuracy and stability for piezoelectric MEMS mirror applications and useful references for the development of micro display technologies.

Key words: Piezoelectric micro mirror; Piezoelectric ceramic; Micro-electro-mechanical systems; Laser beam scanning; AR/VR

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